



Average gate power dissipation ($T_j=125\text{ }^{\circ}\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25\text{ }^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS

ORDERING INFORMATION

<u>J</u>	<u>CT</u>	<u>8</u>	<u>12</u>	<u>C</u>
JieJie Microelectronics Co., Ltd.	SCRs			C:TO-220C
	8:V _{DRM} /V _{RRM} 1800V		I _{T(RMS)} :12A	

MARKING

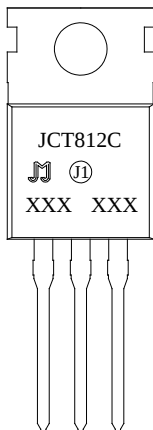
	<table><tr><td></td><td><u>XXX</u></td><td><u>XXX</u></td><td></td></tr><tr><td>Year</td><td>—</td><td>—</td><td>Production</td></tr><tr><td>Month</td><td>—</td><td>—</td><td>Code</td></tr></table>		<u>XXX</u>	<u>XXX</u>		Year	—	—	Production	Month	—	—	Code
	<u>XXX</u>	<u>XXX</u>											
Year	—	—	Production										
Month	—	—	Code										

FIG.1: Maximum power dissipation versus

PACKAGING INFORMATION

	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
	800	15	TO-220C	50	Tube

PACKAGE MECHANICAL DATA



